

ABSTRACT

In the exhaust gas treatment method of the present invention, exhaust gas in an excited state in semiconductor device production equipment is introduced into a plasma treatment unit of a treatment unit under reduced pressure, introduced into a reactor of a reaction removal unit while maintained in an excited state by plasma generated in the plasma treatment unit, and is reacted with a reaction remover composed of particulate calcium oxide filled into the reactor to remove harmful gas components in the exhaust gas. Exhaust gas may also be reacted with the reaction remover after having degraded the harmful gas components by oxidative degradation in the presence of plasma by supplying oxygen to the plasma treatment unit.